

NPN Triple Diffused Planar Silicon Transistor

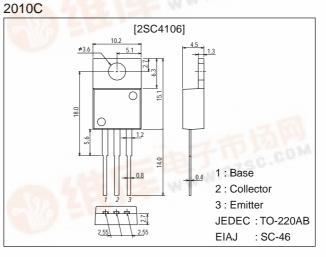


#### **Features**

- · High breakdown voltage and high reliability.
- · Fast switching speed.
- · Wide ASO.
- · Adoption of MBIT process.

## Package Dimensions

# unit:mm



## **Specifications**

#### Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	VCBO		500	V
Collector-to-Emitter Voltage	VCEO		400	V
Emitter-to-Base Voltage	VEBO		7	V
Collector Current	IC		- 7	A
Collector Current (Pulse)	ICP	PW≤300µs, duty cycle≤10%	14	A
Base Current	Ι <sub>Β</sub>		3	A
Collector Dissipation	PC		1.75	W
		Tc=25°C	50	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg	COM	-55 to +150	°C

#### Electrical Characteristics at Ta = 25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
Collector Cutoff Current	I <sub>CBO</sub>	V <sub>CB</sub> =400V, I <sub>E</sub> =0		-	10	μA
Emitter Cutoff Current	IEBO	V <sub>EB</sub> =5V, I <sub>C</sub> =0	200	- 11	10	μA
DC Current Gain	h <sub>FE</sub> 1	V <sub>CE</sub> =5V, I <sub>C</sub> =0.8A	15*		50*	
	h <sub>FE</sub> 2	$V_{CE}=5V, I_{C}=4A$	10			
	h <sub>FE</sub> 3	V <sub>CE</sub> =5V, I <sub>C</sub> =10mA	10			

\*: The h<sub>FE</sub>l of the 2SC4106 is classified as follows. When specifying the h<sub>FE</sub>l rank, specify two ranks or more in principle.

15 L 30 20 M 40 30 N 50

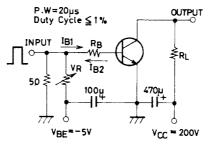
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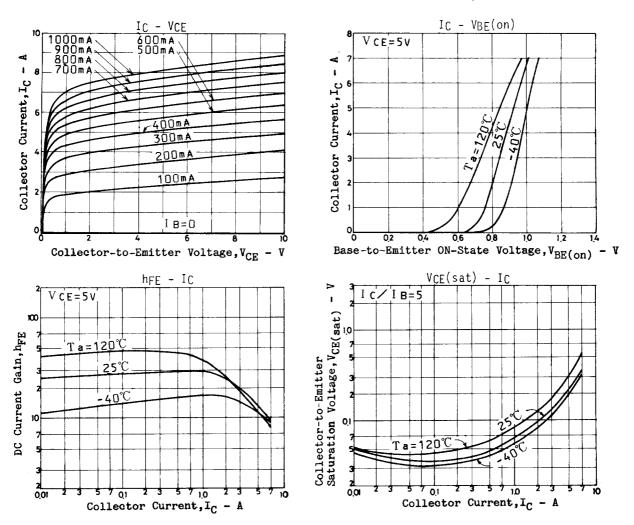
## 2SC4106

Parameter	Symbol	Conditions		Ratings		
	Symbol		min	typ	max	Unit
Collector-to-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =4A, I <sub>B</sub> =0.8A			0.8	V
Base-to-Emitter Saturation Voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> =4A, I <sub>B</sub> =0.8A			1.5	V
Gain-Bandwidth Product	fT	V <sub>CE</sub> =10V, I <sub>C</sub> =0.8A		20		MHz
Output Capacitance	Cob	V <sub>CB</sub> =10V, f=1MHz		80		pF
Collector-to-Base Breakdown Voltage	V <sub>(BR)</sub> CBO	I <sub>C</sub> =1mA, I <sub>E</sub> =0	500			V
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	I <sub>C</sub> =5mA, R <sub>BE</sub> =∞	400			V
Emitter-to-Base Breakdown Voltage	V(BR)EBO	I <sub>E</sub> =1mA, I <sub>C</sub> =0	7			V
Collector-to-Emitter Sustain Voltage	VCEX(sus)	I <sub>C</sub> =3A, I <sub>B1</sub> =0.3A, I <sub>B2</sub> =-1.2A, L=1mH, clamped	400			V
Turn-ON Time	ton	I <sub>C</sub> =5A, I <sub>B1</sub> =1A, I <sub>B2</sub> =-2A, R <sub>L</sub> =40Ω, V <sub>CC</sub> =200V			0.5	μs
Storage Time	<sup>t</sup> stg	I <sub>C</sub> =5A, I <sub>B1</sub> =1A, I <sub>B2</sub> =-2A, R <sub>L</sub> =40Ω, V <sub>CC</sub> =200V			2.5	μs
Fall Time	tf	I <sub>C</sub> =5A, I <sub>B1</sub> =1A, I <sub>B2</sub> =-2A, R <sub>L</sub> =40Ω, V <sub>CC</sub> =200V			0.3	μs

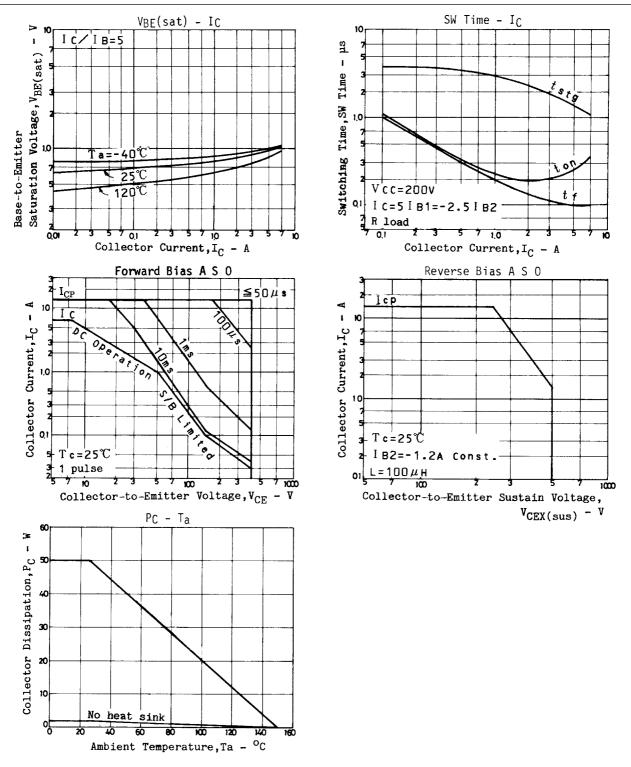
#### **Switching Time Test Circuit**



Unit (resistance :  $\Omega$ , capacitance : F)



### 2SC4106



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